

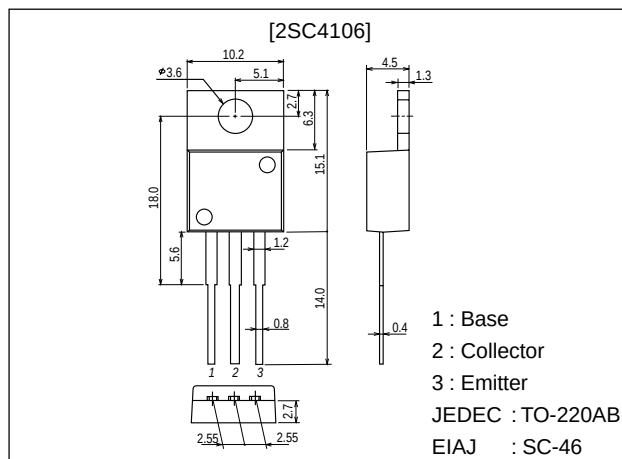
**2SC4106****400V/7A Switching Regulator Applications****Features**

- High breakdown voltage and high reliability.
- Fast switching speed.
- Wide ASO.
- Adoption of MBIT process.

Package Dimensions

unit:mm

2010C

**Specifications****Absolute Maximum Ratings at Ta = 25°C**

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		500	V
Collector-to-Emitter Voltage	V_{CEO}		400	V
Emitter-to-Base Voltage	V_{EBO}		7	V
Collector Current	I_C		7	A
Collector Current (Pulse)	I_{CP}	PW≤300μs, duty cycle≤10%	14	A
Base Current	I_B		3	A
Collector Dissipation	P_C		1.75	W
		Tc=25°C	50	W
Junction Temperature	T_j		150	°C
Storage Temperature	T_{stg}		-55 to +150	°C

Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	$V_{CB}=400V, I_E=0$			10	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=5V, I_C=0$			10	μA
DC Current Gain	h_{FE1}	$V_{CE}=5V, I_C=0.8A$	15*		50*	
	h_{FE2}	$V_{CE}=5V, I_C=4A$	10			
	h_{FE3}	$V_{CE}=5V, I_C=10mA$	10			

* : The h_{FE1} of the 2SC4106 is classified as follows. When specifying the h_{FE1} rank, specify two ranks or more in principle.

15	L	30	20	M	40	30	N	50
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■ Any and all SANYO products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your SANYO representative nearest you before using any SANYO products described or contained herein in such applications.

■ SANYO assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all SANYO products described or contained herein.

SANYO Electric Co.,Ltd. Semiconductor Business Headquarters

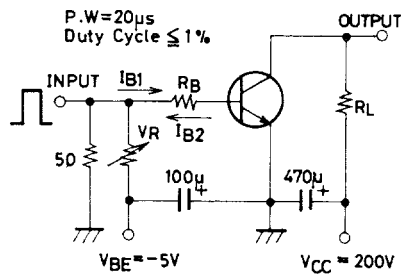
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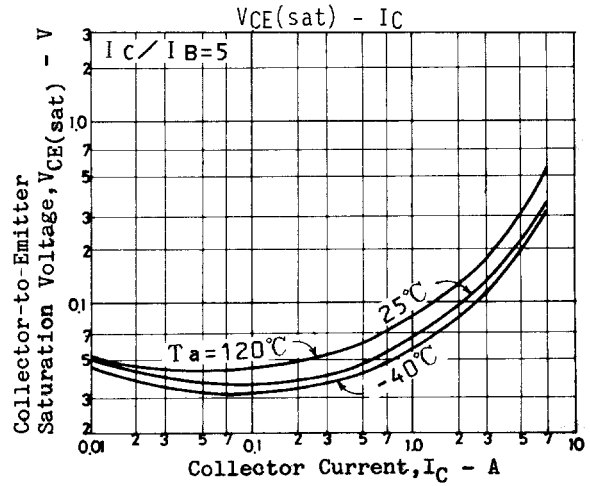
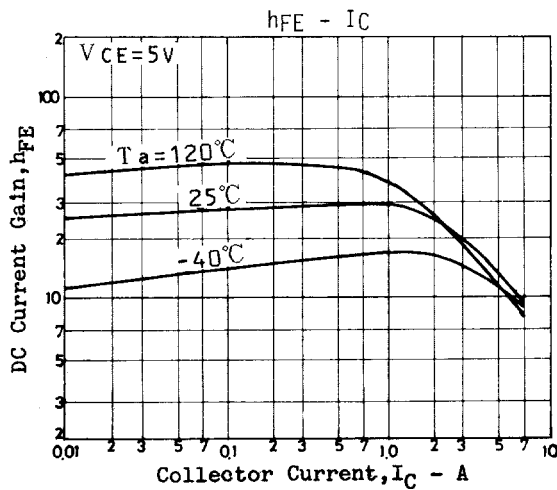
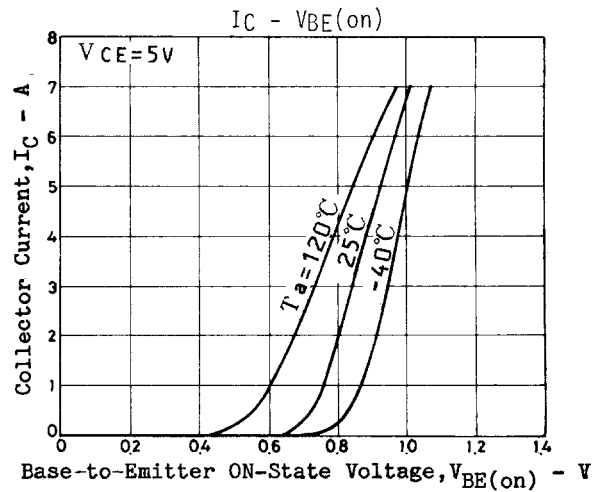
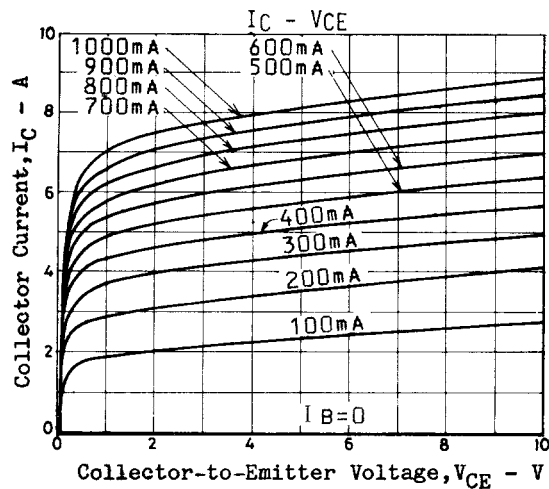
2SC4106

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=4A, I_B=0.8A$			0.8	V
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=4A, I_B=0.8A$			1.5	V
Gain-Bandwidth Product	f_T	$V_{CE}=10V, I_C=0.8A$		20		MHz
Output Capacitance	C_{ob}	$V_{CB}=10V, f=1MHz$		80		pF
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=1mA, I_E=0$	500			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=5mA, R_{BE}=\infty$	400			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=1mA, I_C=0$	7			V
Collector-to-Emitter Sustain Voltage	$V_{CEX(sus)}$	$I_C=3A, I_{B1}=0.3A, I_{B2}=-1.2A, L=1mH, \text{clamped}$	400			V
Turn-ON Time	t_{on}	$I_C=5A, I_{B1}=1A, I_{B2}=-2A, R_L=40\Omega, V_{CC}=200V$			0.5	μs
Storage Time	t_{stg}	$I_C=5A, I_{B1}=1A, I_{B2}=-2A, R_L=40\Omega, V_{CC}=200V$			2.5	μs
Fall Time	t_f	$I_C=5A, I_{B1}=1A, I_{B2}=-2A, R_L=40\Omega, V_{CC}=200V$			0.3	μs

Switching Time Test Circuit



Unit (resistance : Ω , capacitance : F)



2SC4106

